

Dual/Quad Rail-to-Rail Operational Amplifiers

OP295/OP495

FEATURES

Rail-to-Rail Output Swing Single-Supply Operation: +3 V to +36 V Low Offset Voltage: 300 µV Gain Bandwidth Product: 75 kHz High Open-Loop Gain: 1000 V/mV Unity-Gain Stable Low Supply Current/Per Amplifier: 150 µA max

APPLICATIONS

Battery Operated Instrumentation Servo Amplifiers Actuator Drives Sensor Conditioners Power Supply Control

PIN CONNECTIONS



GENERAL DESCRIPTION

Rail-to-rail output swing combined with dc accuracy are the key features of the OP495 quad and OP295 dual CBCMOS operational amplifiers. By using a bipolar front end, lower noise and higher accuracy than that of CMOS designs has been achieved. Both input and output ranges include the negative supply, providing the user "zero-in/zero-out" capability. For users of 3.3 volt systems such as lithium batteries, the OP295/OP495 is specified for three volt operation.

Maximum offset voltage is specified at $300 \,\mu\text{V}$ for +5 volt operation, and the open-loop gain is a minimum of $1000 \,\text{V/mV}$. This yields performance that can be used to implement high accuracy systems, even in single supply designs.

The ability to swing rail-to-rail and supply +15 mA to the load makes the OP295/OP495 an ideal driver for power transistors and "H" bridges. This allows designs to achieve higher efficiencies and to transfer more power to the load than previously possible without the use of discrete components. For applications

that require driving inductive loads, such as transformers, increases in efficiency are also possible. Stability while driving capacitive loads is another benefit of this design over CMOS rail-to-rail amplifiers. This is useful for driving coax cable or large FET transistors. The OP295/OP495 is stable with loads in excess of 300 pF.

The OP295 and OP495 are specified over the extended industrial (-40° C to $+125^{\circ}$ C) temperature range. OP295s are available in 8-pin plastic and ceramic DIP plus SO-8 surface mount packages. OP495s are available in 14-pin plastic and SO-16 surface mount packages. Contact your local sales office for MIL-STD-883 data sheet.

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$\begin{array}{l} \textbf{OP295/OP495-SPECIFICATIONS} \\ \textbf{ELECTRICAL CHARACTERISTICS} (@V_{S} = +5.0 \text{ V}, V_{CM} = +2.5 \text{ V}, T_{A} = +25^{\circ}\text{C} \text{ unless otherwise noted}) \end{array}$

Parameter	Symbol	Conditions	Min	Тур	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	Vos			30	300	μV
0	00	$-40^{\circ}C \le T_A \le +125^{\circ}C$			800	μV
Input Bias Current	I_B			8	20	nA
		$-40^{\circ}C \le T_A \le +125^{\circ}C$			30	nA
Input Offset Current	I _{OS}			± 1	± 3	nA
		$-40^{\circ}C \leq T_A \leq +125^{\circ}C$	_		± 5	nA
Input Voltage Range	V _{CM}		0		+4.0	V
Common-Mode Rejection Ratio	CMRR	$0 \text{ V} \le \text{V}_{\text{CM}} \le 4.0 \text{ V}, -40^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$	90	110		dB
Large Signal Voltage Gain	A_{VO}	$R_{L} = 10 \text{ k}\Omega, \ 0.005 \le V_{OUT} \le 4.0 \text{ V}$	1000	10,000		V/mV
Offert Velter to Deift		$R_L = 10 \text{ k}\Omega, -40^{\circ}\text{C} \le T_A \le +125^{\circ}\text{C}$	500	1	~	V/mV
Offset Voltage Drift	$\Delta V_{OS} / \Delta T$			1	5	µV/°C
OUTPUT CHARACTERISTICS						
Output Voltage Swing High	V _{OH}	$R_{\rm L} = 100 \ \rm k\Omega$ to GND	4.98	5.0		V
		$R_L = 10 \ k\Omega$ to GND	4.90	4.94		V
		$I_{OUT} = 1 \text{ mA}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$		4.7	_	V
Output Voltage Swing Low	V _{OL}	$R_L = 100 \text{ k}\Omega$ to GND		0.7	2	mV
		$R_L = 10 \text{ k}\Omega \text{ to GND}$		0.7	2	mV
	Ŧ	I_{OUT} = 1 mA, -40°C \leq T _A \leq +125°C		90		mV
Output Current	I _{OUT}		±11	±18		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$\pm 1.5 \text{ V} \le \text{V}_{\text{S}} \le \pm 15 \text{ V}$	90	110		dB
		$\pm 1.5 \text{ V} \le \text{V}_{\text{S}} \le \pm 15 \text{ V},$				
	_	$-40^{\circ}C \le T_A \le +125^{\circ}C$	85			dB
Supply Current Per Amplifier	I _{SY}	V_{OUT} = 2.5 V, R_L = ∞ , $-40^\circ C \leq T_A \leq +125^\circ C$			150	μA
DYNAMIC PERFORMANCE						
Skew Rate	SR	$R_{\rm L} = 10 \ \rm k\Omega$		0.03		V/µs
Gain Bandwidth Product	GBP			75		kHz
Phase Margin	θ_{O}			86		Degree
NOISE PERFORMANCE						
Voltage Noise	e _{n p-p}	0.1 Hz to 10 Hz		1.5		μV p-p
Voltage Noise Density	e _n	f = 1 kHz		51		nV/\sqrt{Hz}
Current Noise Density	i _n	f = 1 kHz		< 0.1		pA/√Hz

Specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS (@ $V_s = +3.0 V$, $V_{CM} = +1.5 V$, $T_A = +25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units
INPUT CHARACTERISTICS Offset Voltage Input Bias Current Input Offset Current Input Voltage Range Common-Mode Rejection Ratio Large Voltage Gain Offset Voltage Drift	$V_{OS} \\ I_B \\ I_{OS} \\ V_{CM} \\ CMRR \\ A_{VO} \\ \Delta V_{OS} / \Delta T$	0 V \leq V_{CM} \leq 2.0 V, -40°C \leq T_A \leq +125°C R_L = 10 k\Omega	0 90	$30 \\ 8 \\ \pm 1 \\ 110 \\ 750 \\ 1$	$500 \\ 20 \\ \pm 3 \\ +2.0$	μV nA nA V dB V/mV μV/°C
OUTPUT CHARACTERISTICS Output Voltage Swing High Output Voltage Swing Low	V _{OH} V _{OL}	$R_L = 10$ kΩ to GND $R_L = 10$ kΩ to GND	2.9	0.7	2	V mV
POWER SUPPLY Power Supply Rejection Ratio	PSRR	$\begin{array}{l} \pm 1.5 \ V \leq V_S \leq \pm 15 \ V \\ \pm 1.5 \ V \leq V_S \leq \pm 15 \ V, \\ -40^{\circ}C \leq T_A \leq +125^{\circ}C \end{array}$	90 85	110		dB dB
Supply Current Per Amplifier	I _{SY}	$V_{OUT} = 1.5$ V, $R_L = \infty$, $-40^{\circ}C \le T_A \le +125^{\circ}C$			150	μA
DYNAMIC PERFORMANCE Slew Rate Gain Bandwidth Product Phase Margin	SR GBP θ ₀	$R_{\rm L} = 10 \ {\rm k}\Omega$		0.03 75 85		V/µs kHz Degrees
NOISE PERFORMANCE Voltage Noise Voltage Noise Density Current Noise Density	e _{n p-p} e _n i _n	0.1 Hz to 10 Hz f = 1 kHz f = 1 kHz		1.6 53 <0.1		µV p-p nV/√Hz pA/√Hz

Specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15.0 \text{ V}$, $T_A = +25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage	Vos			30	300	μV
5		$-40^{\circ}C \le T_A \le +125^{\circ}C$			800	μV
Input Bias Current	I _B	$V_{CM} = 0 V$		7	20	nA
		$V_{CM}=0~V,~-40^{\circ}C\leq T_{A}\leq+125^{\circ}C$			30	nA
Input Offset Current	I _{OS}	$V_{CM} = 0 V$		± 1	± 3	nA
		$V_{CM}=0~V,~-40^{\circ}C\leq T_{A}\leq+125^{\circ}C$			± 5	nA
Input Voltage Range	V _{CM}		-15		+13.5	V
Common-Mode Rejection Ratio	CMRR	$-15.0 \text{ V} \le \text{V}_{CM} \le +13.5 \text{ V}, -40^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$	90	110		dB
Large Signal Voltage Gain	A _{VO}	$R_L = 10 \text{ k}\Omega$	1000	4000		V/mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$			1		µV/°C
OUTPUT CHARACTERISTICS						
Output Voltage Swing High	V _{OH}	$R_L = 100 \text{ k}\Omega$ to GND	14.95			V
		$R_L = 10 \ k\Omega$ to GND	14.80			V
Output Voltage Swing Low	V _{OL}	$R_{\rm L} = 100 \ \rm k\Omega \ to \ \rm GND$			-14.95	V
	-	$R_L = 10 \text{ k}\Omega \text{ to GND}$			-14.85	V .
Output Current	I _{OUT}		±15	± 25		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{S} = \pm 1.5 \text{ V to } \pm 15 \text{ V}$	90	110		dB
115 5		$V_{S} = \pm 1.5 \text{ V to } \pm 15 \text{ V}, -40^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$	85			dB
Supply Current	I _{SY}	$V_0 = 0 V, R_1 = \infty, V_S = \pm 18 V,$				
		$-40^{\circ}C \le T_A \le +125^{\circ}C$			175	μA
Supply Voltage Range	Vs		+3 (±1.5)		$+36 (\pm 18)$	V
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_{I} = 10 \text{ k}\Omega$		0.03		V/us
Gain Bandwidth Product	GBP	$M_{\rm L} = 10 \text{ M}_{22}$		85		kHz
Phase Margin				83		Degrees
	V0			00		Digites
NOISE PERFORMANCE						
Voltage Noise	e _{n p-p}	0.1 Hz to 10 Hz		1.25		μV p-p
Voltage Noise Density	en	f = 1 kHz		45		nV/√Hz
Current Noise Density	i _n	f = 1 kHz		< 0.1		pA/\sqrt{Hz}

Specifications subject to change without notice.

WAFER TEST LIMITS (@ V_s = +5.0 V, V_{CM} = 2.5 V, T_A = +25°C unless otherwise noted)

Parameter	Symbol	Conditions	Limit	Units
Offset Voltage	Vos		300	μV max
Input Bias Current	IB		20	nA max
Input Offset Current	I _{OS}		±2	nA max
Input Voltage Range ¹	V _{CM}		0 to +4	V min
Common-Mode Rejection Ratio	CMRR	$0 \text{ V} \le V_{CM} \le 4 \text{ V}$	90	dB min
Power Supply Rejection Ratio	PSRR	$\pm 1.5 \text{ V} \le \text{V}_{\text{S}} \le \pm 15 \text{ V}$	90	μV/V
Large Signal Voltage Gain	A _{VO}	$R_{\rm L} = 10 \ \rm k\Omega$	1000	V/mV min
Output Voltage Swing High	V _{OH}	$R_{\rm L} = 10 \ \rm k\Omega$	4.9	V min
Supply Current Per Amplifier	I _{SY}	$V_{OUT} = 2.5 \text{ V}, \text{ R}_{L} = \infty$	150	μA max

NOTES

Electrical tests and wafer probe to the limits shown. Due to variations in assembly methods and normal yield loss, yield after packaging is not guaranteed for standard product dice. Consult factory to negotiate specifications based on dice lot qualifications through sample lot assembly and testing. 1 Guaranteed by CMRR test.

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Model	Temperature Range	Package Description	Package Option
OP295GP OP295GS OP295GBC	-40°C to +125°C -40°C to +125°C +25°C		N-8 SO-8	OP495GP OP495GS OP495GBC	-40°C to +125°C	14-Pin Plastic DIP 16-Pin SOL DICE	N-14 R-16

ABSOLUTE MAXIMUM RATINGS¹

Package Type	$\theta_{JA}{}^3$	θ _{JC}	Unit
Lead Temperature Range	(Soldering, 6	60 Sec)	+300°C
P, S Package		65°C	C to +150°C
Junction Temperature Rar	ıge		
OP295G, OP495G		40°C	C to +125°C
Operating Temperature Ra	ange		
P, S Package		65°C	C to +150°C
Storage Temperature Rang	ge		
Output Short-Circuit Dura			Indefinite
Differential Input Voltage ²			
Input Voltage ²			
Supply Voltage			±18 V

Fackage Type	UJA	olC	Unit
8-Pin Plastic DIP (P)	103	43	°C/W
8-Pin SOIC (S)	158	43	°C/W
14-Pin Plastic DIP (P)	83	39	°C/W
16-Pin SO (S)	98	30	°C/W

NOTES

¹Absolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

 2 For supply voltages less than ± 18 V, the absolute maximum input voltage is equal to the supply voltage.

 ${}^{3}\theta_{JA}$ is specified for the worst case conditions, i.e., θ_{JA} is specified for device in socket for cerdip, P-DIP, and LCC packages; θ_{JA} is specified for device soldered in circuit board for SOIC package.

DICE CHARACTERISTICS



OP295 Die Size 0.066 × 0.080 inch, 5,280 sq. mils. Substrate (Die Backside) Is Connected to V+. Transistor Count, 74.



OP495 Die Size 0.113 × 0.083 inch, 9,380 sq. mils. Substrate (Die Backside) Is Connected to V+. Transistor Count, 196.



Typical Characteristics

Supply Current Per Amplifier vs. Temperature



Output Voltage Swing vs. Temperature



Output Voltage Swing vs. Temperature







OP295 TC-V_{OS} Distribution

Typical Characteristics-0P295/0P495



Output Voltage Swing vs. Temperature



OP495 Input Offset (Vos) Distribution



OP495 TC-V_{OS} Distribution

0P295/0P495–Typical Characteristics



Input Bias Current vs. Temperature



Open-Loop Gain vs. Temperature



Output Current vs. Temperature



Open-Loop Gain vs. Temperature



Output Voltage to Supply Rail vs. Load Current

APPLICATIONS

Rail-to-Rail Applications Information

The OP295/OP495 has a wide common-mode input range extending from ground to within about 800 mV of the positive supply. There is a tendency to use the OP295/OP495 in buffer applications where the input voltage could exceed the commonmode input range. This may initially appear to work because of the high input range and rail-to-rail output range. But above the common-mode input range the amplifier is, of course, highly nonlinear. For this reason it is always required that there be some minimal amount of gain when rail-to-rail output swing is desired. Based on the input common-mode range this gain should be at least 1.2.

Low Drop-Out Reference

The OP295/OP495 can be used to gain up a 2.5 V or other low voltage reference to 4.5 volts for use with high resolution A/D converters that operate from +5 volt only supplies. The circuit in Figure 1 will supply up to 10 mA. Its no-load drop-out voltage is only 20 mV. This circuit will supply over 3.5 mA with a +5 volt supply.



Figure 1. 4.5 Volt, Low Drop-Out Reference

Low Noise, Single Supply Preamplifier

Most single supply op amps are designed to draw low supply current, at the expense of having higher voltage noise. This tradeoff may be necessary because the system must be powered by a battery. However, this condition is worsened because all circuit resistances tend to be higher; as a result, in addition to the op amp's voltage noise, Johnson noise (resistor thermal noise) is also a significant contributor to the total noise of the system.

The choice of monolithic op amps that combine the characteristics of low noise and single supply operation is rather limited. Most single supply op amps have noise on the order of 30 nV/ $\sqrt{\text{Hz}}$ to 60 nV/ $\sqrt{\text{Hz}}$ and single supply amplifiers with noise below 5 nV/ $\sqrt{\text{Hz}}$ do not exist.

In order to achieve both low noise and low supply voltage operation, discrete designs may provide the best solution. The circuit on Figure 2 uses the OP295/OP495 rail-to-rail amplifier and a matched PNP transistor pair—the MAT03—to achieve zero-in/zero-out single supply operation with an input voltage noise of $3.1 \text{ nV}/\sqrt{\text{Hz}}$ at 100 Hz. R5 and R6 set the gain of 1000, making this circuit ideal for maximizing dynamic range when amplifying low level signals in single supply applications. The OP295/OP495 provides rail-to-rail output swings, allowing this circuit to operate with 0 to 5 volt outputs. Only half of the OP295/OP495 is used, leaving the other uncommitted op amp for use elsewhere.



Figure 2. Low Noise Single Supply Preamplifier

The input noise is controlled by the MAT03 transistor pair and the collector current level. Increasing the collector current reduces the voltage noise. This particular circuit was tested with 1.85 mA and 0.5 mA of current. Under these two cases, the input voltage noise was 3.1 nV/ $\sqrt{\text{Hz}}$ and 10 nV/ $\sqrt{\text{Hz}}$, respectively. The high collector currents do lead to a tradeoff in supply current, bias current, and current noise. All of these parameters will increase with increasing collector current. For example, typically the MAT03 has an $h_{FE} = 165$. This leads to bias currents of 11 µA and 3 µA, respectively. Based on the high bias currents, this circuit is best suited for applications with low source impedance such as magnetic pickups or low impedance strain gages. Furthermore, a high source impedance will degrade the noise performance. For example, a 1 k Ω resistor generates 4 nV/ \sqrt{Hz} of broadband noise, which is already greater than the noise of the preamp.

The collector current is set by R1 in combination with the LED and Q2. The LED is a 1.6 V "Zener" that has a temperature coefficient close to that of Q2's base-emitter junction, which provides a constant 1.0 V drop across R1. With R1 equal to 270Ω , the tail current is 3.7 mA and the collector current is half that, or 1.85 mA. The value of R1 can be altered to adjust the collector current. Whenever R1 is changed, R3 and R4 should also be adjusted. To maintain a common-mode input range that includes ground, the collectors of the Q1 and Q2 should not go above 0.5 V-otherwise they could saturate. Thus, R3 and R4 have to be small enough to prevent this condition. Their values and the overall performance for two different values of R1 are summarized in Table I. Lastly, the potentiometer, R8, is needed to adjust the offset voltage to null it to zero. Similar performance can be obtained using an OP90 as the output amplifier with a savings of about 185 µA of supply current. However, the output swing will not include the positive rail, and the bandwidth will reduce to approximately 250 Hz.

	I _C = 1.85 mA	I _C = 0.5 mA
R1	270 Ω	1.0 kΩ
R3, R4	200 Ω	910 Ω
e _n @ 100 Hz	$3.15 \text{ nV}/\sqrt{\text{Hz}}$	8.6 nV/√Hz
e _n @ 10 Hz	$4.2 \text{ nV}/\sqrt{\text{Hz}}$	10.2 nV/√Hz
I _{SY}	4.0 mA	1.3 mA
I _B	11 µA	3 μA
Bandwidth	1 kHz	1 kHz
Closed-Loop Gain	1000	1000

Table I. Single Supply Low Noise Preamp Performance

Driving Heavy Loads

The OP295/OP495 is well suited to drive loads by using a power transistor, Darlington or FET to increase the current to the load. The ability to swing to either rail can assure that the device is turned on hard. This results in more power to the load and an increase in efficiency over using standard op amps with their limited output swing. Driving power FETs is also possible with the OP295/OP495 because of its ability to drive capacitive loads of several hundred picofarads without oscillating.

Without the addition of external transistors the OP295/OP495 can drive loads in excess of ± 15 mA with ± 15 or ± 30 volt supplies. This drive capability is somewhat decreased at lower supply voltages. At ± 5 volt supplies the drive current is ± 11 mA.

Driving motors or actuators in two directions in a single supply application is often accomplished using an "H" bridge. The principle is demonstrated in Figure 3a. From a single +5 volt supply this driver is capable of driving loads from 0.8 V to 4.2 V in both directions. Figure 3b shows the voltages at the inverting and noninverting outputs of the driver. There is a small crossover glitch that is frequency dependent and would not cause problems







Figure 3b. "H" Bridge Outputs

unless this was a low distortion application such as audio. If this is used to drive inductive loads, be sure to add diode clamps to protect the bridge from inductive kickback.

Direct Access Arrangement

OP295/OP495 can be used in a single supply Direct Access Arrangement (DAA) as is shown an in Figure 4. This figure shows a portion of a typical DM capable of operating from a single +5 volt supply and it may also work on +3 volt supplies with minor modifications. Amplifiers A2 and A3 are configured so that the transmit signal TXA is inverted by A2 and is not inverted by A3. This arrangement drives the transformer differentially so that the drive to the transformer is effectively doubled over a single amplifier arrangement. This application takes advantage of the OP295/OP495's ability to drive capacitive loads, and to save power in single supply applications.



Figure 4. Direct Access Arrangement

A Single Supply Instrumentation Amplifier

The OP295/OP495 can be configured as a single supply instrumentation amplifier as in Figure 5. For our example, V_{REF} is set equal to $\frac{V+}{2}$ and V_{O} is measured with respect to V_{REF} . The input common-mode voltage range includes ground and the output swings to both rails.



Figure 5. Single Supply Instrumentation Amplifier

Resistor R_G sets the gain of the instrumentation amplifier. Minimum gain is 6 (with no R_G). All resistors should be matched in absolute value as well as temperature coefficient to maximize

common-mode rejection performance and minimize drift. This instrumentation amplifier can operate from a supply voltage as low as 3 volts.

A Single Supply RTD Thermometer Amplifier

This RTD amplifier takes advantage of the rail-to-rail swing of the OP295/OP495 to achieve a high bridge voltage in spite of a low 5 V supply. The OP295/OP495 amplifier servos a constant 200 μ A current to the bridge. The return current drops across the parallel resistors 6.19 k Ω and the 2.55 M Ω , developing a voltage that is servoed to 1.235 V, which is established by the AD589 bandgap reference. The 3-wire RTD provides an equal line resistance drop in both 100 Ω legs of the bridge, thus improving the accuracy.

The AMP04 amplifies the differential bridge signal and converts it to a single-ended output. The gain is set by the series resistance of the 332 Ω resistor plus the 50 Ω potentiometer. The gain scales the output to produce a 4.5 V full scale. The 0.22 μF capacitor to the output provides a 7 Hz low-pass filter to keep noise at a minimum.



Figure 6. Low Power RTD Amplifier

A Cold Junction Compensated, Battery Powered Thermocouple Amplifier

The OP295/OP495's 150 μ A quiescent current per amplifier consumption makes it useful for battery powered temperature measuring instruments. The K-type thermocouple terminates into an isothermal block where the terminated junctions' ambient temperatures can be continuously monitored and corrected by summing an equal but opposite thermal EMF to the amplifier, thereby canceling the error introduced by the cold junctions.



Figure 7. Battery Powered, Cold-Junction Compensated Thermocouple Amplifier

To calibrate, immerse the thermocouple measuring junction in a 0°C ice bath, adjust the 500 Ω Zero Adjust pot to zero volts out. Then immerse the thermocouple in a 250°C temperature bath or oven and adjust the Scale Adjust pot for an output voltage of 2.50 V, which is equivalent to 250°C. Within this temperature range, the K-type thermocouple is quite accurate and produces a fairly linear transfer characteristic. Accuracy of $\pm 3^\circ$ C is achievable without linearization.

Even if the battery voltage is allowed to decay to as low as 7 volts, the rail-to-rail swing allows temperature measurements to 700°C. However, linearization may be necessary for temperatures above 250°C where the thermocouple becomes rather nonlinear. The circuit draws just under 500 μ A supply current from a 9 V battery.

A 5 V Only, 12-Bit DAC That Swings 0 V to 4.095 V

Figure 8 shows a complete voltage output DAC with wide output voltage swing operating off a single +5 V supply. The serial input 12-bit D/A converter is configured as a voltage output device with the 1.235 V reference feeding the current output pin (I_{OUT}) of the DAC. The V_{REF} which is normally the input now becomes the output.

The output voltage from the DAC is the binary weighted voltage of the reference, which is gained up by the output amplifier such that the DAC has a 1 mV per bit transfer function.



Figure 8. A 5 Volt 12-Bit DAC with 0 V to +4.095 Output Swing

4-20 mA Current Loop Transmitter

Figure 9 shows a self powered 4–20 mA current loop transmitter. The entire circuit floats up from the single supply (12 V to 36 V) return. The supply current carries the signal within the 4 to 20 mA range. Thus the 4 mA establishes the baseline



Figure 9. 4-20 mA Current Loop Transmitter

current budget with which the circuit must operate. This circuit consumes only 1.4 mA maximum quiescent current, making 2.6 mA of current available to power additional signal conditioning circuitry or to power a bridge circuit.

A 3 Volt Low-Dropout Linear Voltage Regulator

Figure 10 shows a simple 3 V voltage regulator design. The regulator can deliver 50 mA load current while allowing a 0.2 V dropout voltage. The OP295/OP495's rail-to-rail output swing handily drives the MJE350 pass transistor without requiring special drive circuitry. At no load, its output can swing less than the pass transistor's base-emitter voltage, turning the device nearly off. At full load, and at low emitter-collector voltages, the transistor beta tends to decrease. The additional base current is easily handled by the OP295/OP495 output.

The amplifier servos the output to a constant voltage, which feeds a portion of the signal to the error amplifier.

Higher output current, to 100 mA, is achievable at a higher dropout voltage of 3.8 V.



Figure 10. 3 V Low Dropout Voltage Regulator

Figure 11 shows the regulator's recovery characteristic when its output underwent a 20 mA to 50 mA step current change.



Figure 11. Output Step Load Current Recovery

Low-Dropout, 500 mA Voltage Regulator with Fold-Back Current Limiting

Adding a second amplifier in the regulation loop as shown in Figure 12 provides an output current monitor as well as fold-back current limiting protection.

Amplifier A1 provides error amplification for the normal voltage regulation loop. As long as the output current is less than 1 ampere, amplifier A2's output swings to ground, reverse biasing the diode and effectively taking itself out of the circuit. However, as the output current exceeds 1 amp, the voltage that develops across the 0.1 Ω sense resistor forces the amplifier A2's output to go high, forward-biasing the diode, which in turn closes the

current limit loop. At this point A2's lower output resistance dominates the drive to the power MOSFET transistor, thereby effectively removing the A1 voltage regulation loop from the circuit.

If the output current greater than 1 amp persists, the current limit loop forces a reduction of current to the load, which causes a corresponding drop in output voltage. As the output voltage drops, the current limit threshold also drops fractionally, resulting in a decreasing output current as the output voltage decreases, to the limit of less than 0.2 A at 1 V output. This "fold-back" effect reduces the power dissipation considerably during a short circuit condition, thus making the power supply far more forgiving in terms of the thermal design requirements. Small heat sinking on the power MOSFET can be tolerated.

The OP295's rail-to-rail swing exacts higher gate drive to the power MOSFET, providing a fuller enhancement to the transistor. The regulator exhibits 0.2 V dropout at 500 mA of load current. At 1 amp output, the dropout voltage is typically 5.6 volts.



Figure 12. Low Dropout, 500 mA Voltage Regulator with Fold-Back Current Limiting

Square Wave Oscillator

The circuit in Figure 13 is a square wave oscillator (note the positive feedback). The rail-to-rail swing of the OP295/OP495 helps maintain a constant oscillation frequency even if the supply voltage varies considerably. Consider a battery powered system where the voltages are not regulated and drop over time. The rail-to-rail swing ensures that the noninverting input sees the full V+/2, rather than only a fraction of it.

The constant frequency comes from the fact that the 58.7 k Ω feedback sets up Schmitt Trigger threshold levels that are directly proportional to the supply voltage, as are the RC charge voltage levels. As a result, the RC charge time, and therefore the frequency, remains constant independent of supply voltage. The slew rate of the amplifier limits the oscillation frequency to a maximum of about 800 Hz at a +5 V supply.

Single Supply Differential Speaker Driver

Connected as a differential speaker driver, the OP295/OP495 can deliver a minimum of 10 mA to the load. With a 600 Ω load, the OP295/OP495 can swing close to 5 volts peak-to-peak across the load.







Figure 14. Single Supply Differential Speaker Driver

High Accuracy, Single-Supply, Low Power Comparator The OP295/OP495 makes an accurate open-loop comparator. With a single +5 V supply, the offset error is less than 300 μ V. Figure 15 shows the OP295/OP495's response time when operating open-loop with 4 mV overdrive. It exhibits a 4 ms response time at the rising edge and a 1.5 ms response time at the falling edge.



Figure 15. Open-Loop Comparator Response Time with 5 mV Overdrive

OP295/OP495 SPICE MODEL Macro-Model

* Nod	e Assi	gnmei	nts				
*		0		oninvert	ing Inp	ut	
*				Inverting Input			
*						ve Supp	oly
*						Negat	ive Supply
*							Output
*							-
*							
.SUBC	CKT (OP295	5 İ	2	99	50	20
*							
* INP	UT S	ГAGE	1				
*							
I1	99	4	2E-6				
R1	1	6	5E3				

R2 CIN IOS D1 D2 EOS Q1 Q2 R3 R4 *	2 1 5 6 7 8 9 8 9	5 2 3 3 6 5 7 50 50	5E3 2E-12 0.5E-9 DZ DZ POLY (1) (31,39) 30E-6 0.024 4 QP 4 QP 25.8E3 25.8E3
* GAIN *	N STA	AGE	
R7 G1 EREF R5 R6	99 39	98 10 0 39 50	270E6 POLY (1) (9,8) -4.26712E-9 27.8E-6 (39, 0) 1 100E3 100E3
* COM *	IMOI	N MC	DDE STAGE
R12 R13	30 30 31	98 31 98	POLY(2) (1,39) (2,39) 0 0.5 0.5 1E6 100
* * OUT *	PUT	STA	GE
I2	18	50	1.59E-6
V2 Q4	99 10	12 14	DC 2.2763 50 QNA 1.0
R11	14	50	33
M3 M4	15 13	10 10	13 13 MN L=9E-6 W=102E-6 AD=15E-10 AD=15E-10 50 50 MN L=9E-6 W=50E-6 AD=75E-11 AS=75E-11
D8	10	22	DX
V3 M2	22 20	50 10	DC 6 14 14 MN L=9E-6 W=2000E-6 AD=30E-9 AS=30E-9
Q5	17	17	99 QPA 1.0
Q6 R8	18 18	17	99 QPA 4.0 2.2E6
Q7	18	99 19	99 QPA 1.0
R9	99	19	8
C2 M6	18 15	99 12	20E-12 17 99 MP L=9E-6 W=27E-6 AD=405E-12 AS=405E-12
M1	20	12	$\begin{array}{cccccccccccccccccccccccccccccccccccc$
D4	21	18	DX
V4 R10	99 10	21 11	DC 6 6E3
C3	11	20	50E-12
+ ISE= + ISC=	2.571 6.9E	E-13 I	IPN (IS=1.19E-16 BF=253 NF=0.99 VAF=193 IKF=2.76E-3 NE=5 BR=0.4 NR=0.988 VAR=15 IKR=1.465E-4 IC=0.99 RB=2.0E3 IRB=7.73E-6 RBM=132.8 RE=4
RC=20 + CJE=		-13 V	'JE=0.573 MJE=0.364 FC=0.5 CJC=1.64E-13 VJC=0.534
.MODI + ISE=	=1.37] EL Q =1.09] =7.58]	PA PI E-14 I	VJS=0.59 MJS=0.5 TF=0.43E-9 PTF=30) NP (IS=5.21E-17 BF=131 NF=0.99 VAF=62 IKF=8.35E-4 NE=2.61 BR=0.5 NR=0.984 VAR=15 IKR=3.96E-5 NC=0.985 RB=1.52E3 IRB=1.67E-5 RBM=368.5 RE=6.31
	-1.1E	-13 V	JE=0.745 MJE=0.33 FC=0.5 CJC=2.37E-13 VJC=0.762
+ CJS = .MODI + TOX	=7.11 EL M =8.51	IN NI E-8 Li	VJS=0.45 MJS=0.412 TF=1.0E-9 PTF=30) MOS (LEVEL=3 VTO=1.3 RS=0.3 RD=0.3 D=1.48E-6 NSUB=1.53E16 UO=650 DELTA=10 VMAX=2E5
PB=0.8	337		APPA=0.8 ETA=0.066 THETA=0.01 TPG=1 CJ=2.9E-4
.MODI + TOX	EL M =9.5	P PN E-8 L	N=0.5E-9 MJSW=0.33) 1OS (LEVEL=3 VTO=-1.1 RS=0.7 RD=0.7 .D=1.4E-6 NSUB=2.4E15 UO=650 DELTA=5.6 VMAX=1E5 .APPA=1.7 ETA=0.71 THETA=5.9E-3 TPG=-1 CJ=1.55E-4
	0.442		N=0.4E-9 MJSW=0.33) IS=1E-15)
.MODI	EL D	ZD (IS=1E-15, BV=7)
.MODI .ENDS	•	r pn	P (BF=125)
_			

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm)

8 Lead Plastic DIP (P Suffix)

Suffix)

8-Lead Narrow-Body SO (S Suffix)



14-Lead Plastic DIP (P Suffix)





16-Lead Wide-Body SO (S Suffix)

